

# Power Transistor (–100V , –2A)

## 2SB1316

### ●Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SD2195 / 2SD1980.

### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	–100	V
Collector-emitter voltage	V <sub>CEO</sub>	–100	V
Emitter-base voltage	V <sub>EB0</sub>	–8	V
Collector current	I <sub>c</sub>	–2	A(DC)
		–3	A(Pulse) *1
Collector power dissipation	P <sub>c</sub>	2	W
		1	W
		10	W(Tc=25°C)
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	–55 to +150	°C

\*1 Single pulse Pw=100ms

\*2 When mounted on a 40 x 40 x 0.7 mm ceramic board.

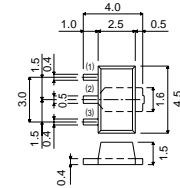
### ●Packaging specifications and hFE

Type	2SB1580	2SB1316
Package	MPT3	CPT3
hFE	1k to 10k	1k to 10k
Marking	BN*	–
Code	T100	TL
Basic ordering unit (pieces)	1000	2500

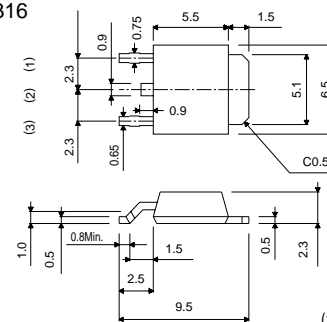
\* Denotes hFE

### ●External dimensions (Unit : mm)

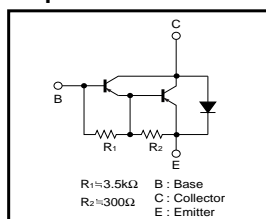
2SB1580

ROHM : MPT3  
EIAJ : SC-62(1) Base  
(2) Collector  
(3) Emitter

2SB1316

ROHM : CPT3  
EIAJ : SC-63  
TO-252(DPAK)(1) Base  
(2) Collector  
(3) Emitter

### ●Equivalent circuit



### ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	–100	–	–	V	I <sub>c</sub> = –50μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	–100	–	–	V	I <sub>c</sub> = –5mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	–10	–	–	V	I <sub>E</sub> = –5mA
Collector cutoff current	I <sub>cbo</sub>	–	–	–10	μA	V <sub>CB</sub> = –100V
Emitter cutoff current	I <sub>ebo</sub>	–	–	–3	mA	V <sub>EB</sub> = –7V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	–	–	–1.5	V	I <sub>c</sub> /I <sub>E</sub> = –1A/–1mA
DC current transfer ratio	h <sub>FE</sub>	1000	–	10000	–	V <sub>CE</sub> = –2V, I <sub>c</sub> = –1A
Transition frequency	f <sub>T</sub>	–	50	–	MHz	V <sub>CE</sub> = –5V, I <sub>E</sub> = 0.1A, f = 30MHz
Output capacitance	C <sub>ob</sub>	–	35	–	pF	V <sub>CB</sub> = –10V, I <sub>E</sub> = 0A, f = 1MHz

\* Measured using pulse current.

Transistors

●Electrical characteristics curve

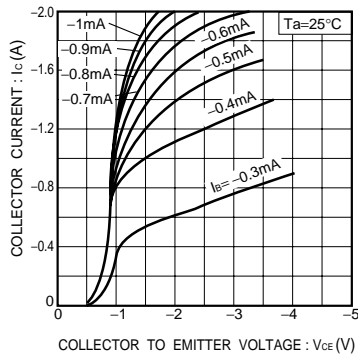


Fig.1 Grounded emitter output characteristics

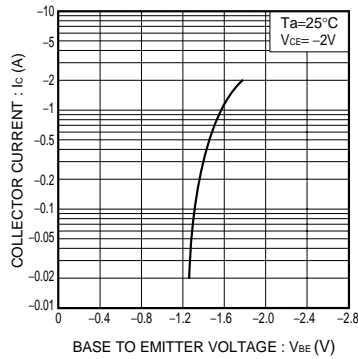


Fig.2 Grounded emitter propagation characteristics

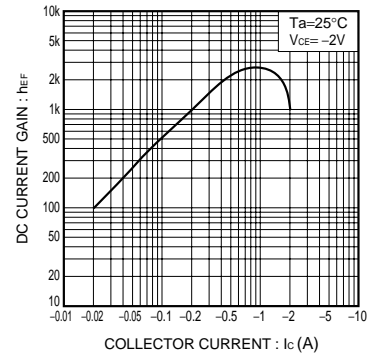


Fig.3 DC current gain vs. collector current

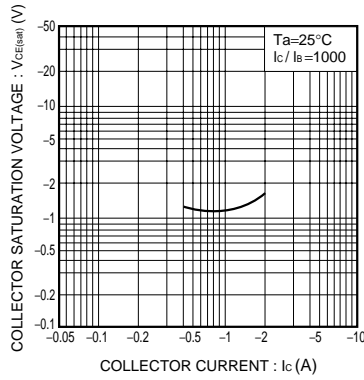


Fig.4 Collector-emitter saturation voltage vs. collector current

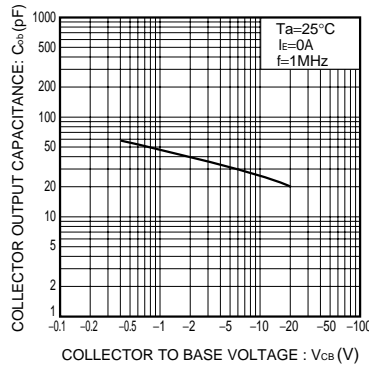


Fig.5 Collector output capacitance vs. collector-base voltage

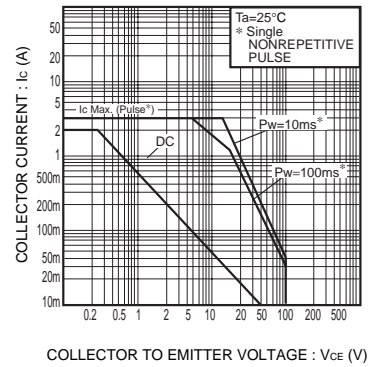


Fig.6 Safe Operating area (2SB1580)

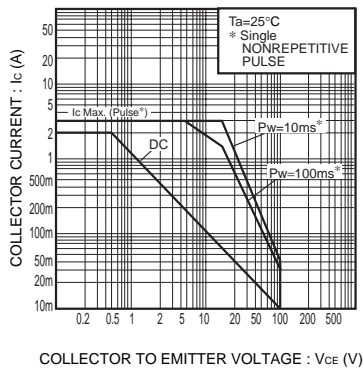


Fig.7 Safe Operating area (2SB1316)

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